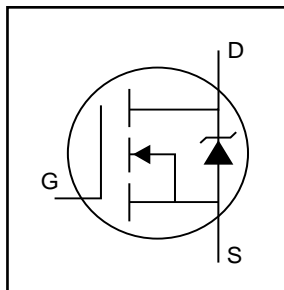


- Logic-Level Gate Drive
- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

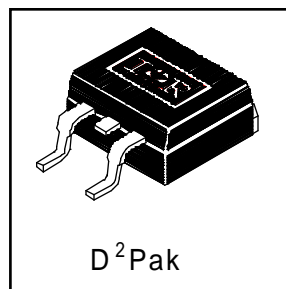


$V_{DSS} = 30V$
$R_{DS(on)} = 0.04\Omega$
$I_D = 24A$

**Description**

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D<sup>2</sup>PAK is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ⑤	24	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ⑤	17	
$I_{DM}$	Pulsed Drain Current ①	96	
$P_D @ T_C = 25^\circ C$	Power Dissipation	45	W
	Linear Derating Factor	0.30	W/°C
$V_{GS}$	Gate-to-Source Voltage	±16	V
$E_{AS}$	Single Pulse Avalanche Energy ②⑤	77	mJ
$I_{AR}$	Avalanche Current①	14	A
$E_{AR}$	Repetitive Avalanche Energy①	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	3.5	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

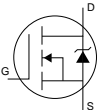
**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	3.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady-state)**	—	—	40	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.030	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.040	$\Omega$	$V_{GS} = 10V, I_D = 14A$ ④
		—	—	0.060		$V_{GS} = 4.5V, I_D = 12A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	6.4	—	—	S	$V_{DS} = 25V, I_D = 14A$ ⑤
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
$Q_g$	Total Gate Charge	—	—	15	nC	$I_D = 14A$
$Q_{gs}$	Gate-to-Source Charge	—	—	4.6		$V_{DS} = 24V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	9.3		$V_{GS} = 4.5V$ , See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	8.5	—	ns	$V_{DD} = 15V$
$t_r$	Rise Time	—	140	—		$I_D = 14A$
$t_{d(off)}$	Turn-Off Delay Time	—	12	—		$R_G = 12\Omega, V_{GS} = 4.5V$
$t_f$	Fall Time	—	20	—		$R_D = 1.0\Omega$ , See Fig. 10 ④⑤
$L_S$	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
$C_{iss}$	Input Capacitance	—	450	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	210	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	110	—		$f = 1.0\text{MHz}$ , See Fig. 5⑤

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	24	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	96		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 14A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	65	97	ns	$T_J = 25^\circ\text{C}, I_F = 14A$
$Q_{rr}$	Reverse Recovery Charge	—	140	210	nC	$di/dt = 100A/\mu s$ ④⑤
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

### Notes:

① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

②  $V_{DD} = 15V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 570\mu H$   
 $R_G = 25\Omega$ ,  $I_{AS} = 14A$ . (See Figure 12)

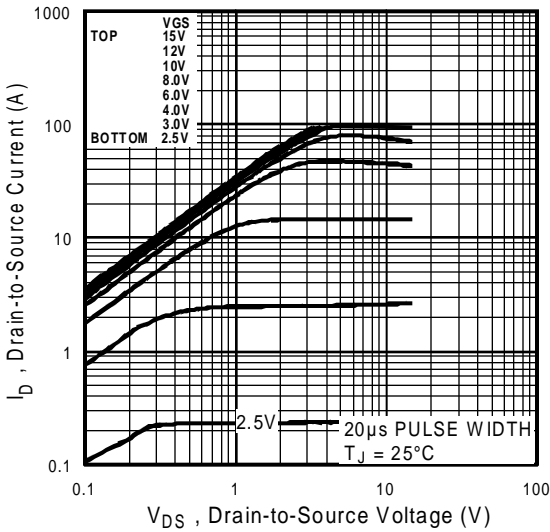
\*\* When mounted on 1" square PCB ( FR-4 or G-10 Material ).

For recommended footprint and soldering techniques refer to application note #AN-994.

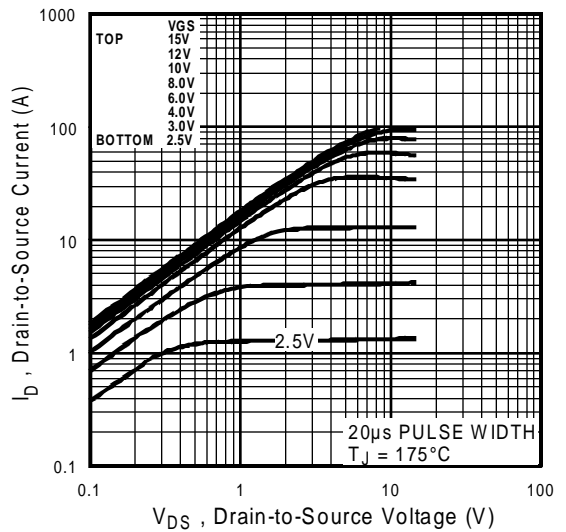
③  $I_{SD} \leq 14A$ ,  $di/dt \leq 140A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

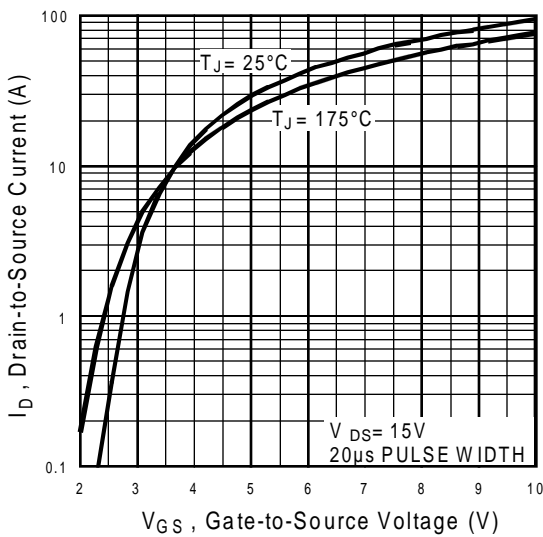
⑤ Uses IRL2703 data and test conditions.



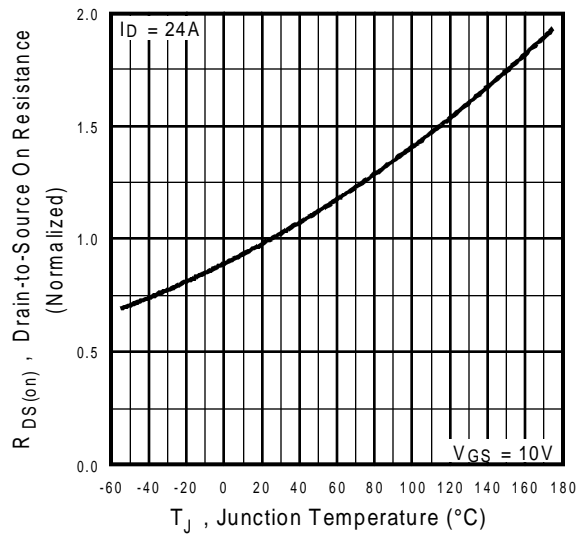
**Fig 1.** Typical Output Characteristics



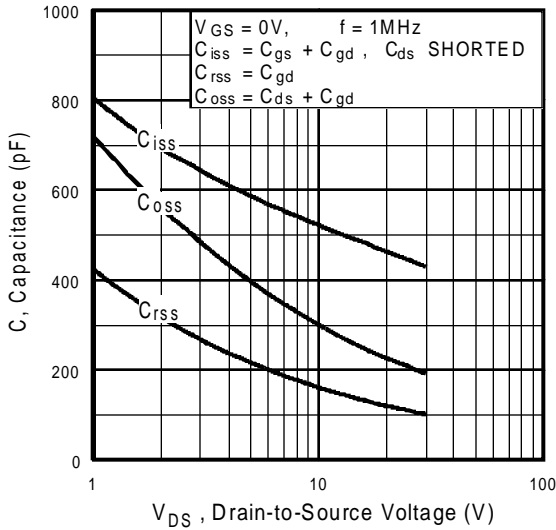
**Fig 2.** Typical Output Characteristics



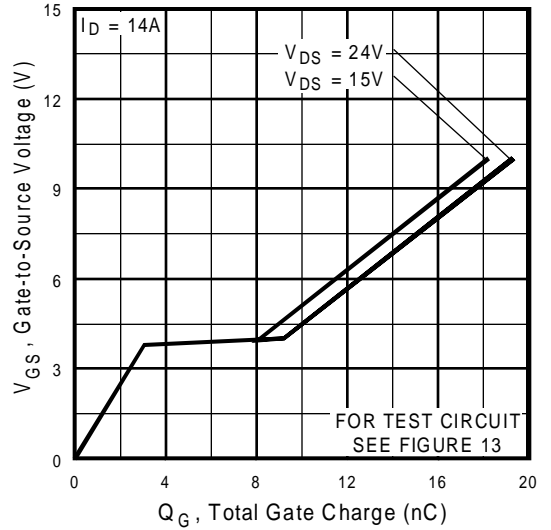
**Fig 3.** Typical Transfer Characteristics



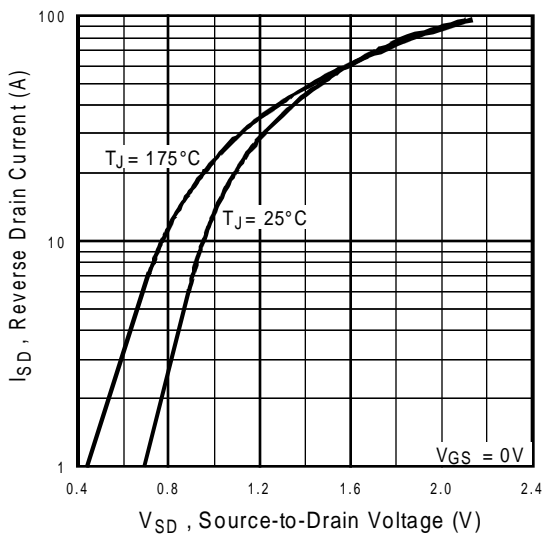
**Fig 4.** Normalized On-Resistance Vs. Temperature



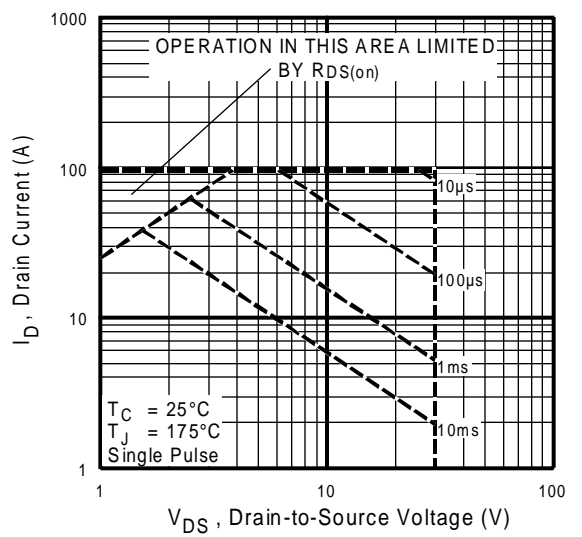
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



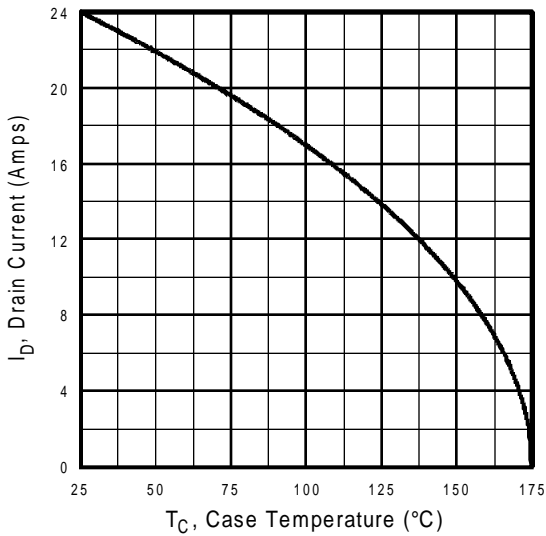
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



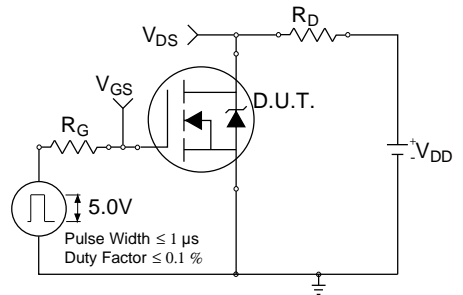
**Fig 7.** Typical Source-Drain Diode Forward Voltage



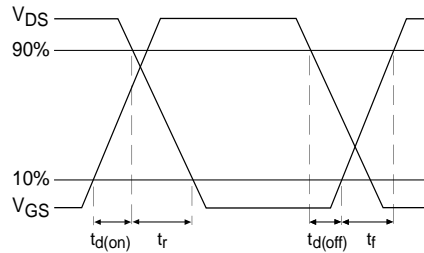
**Fig 8.** Maximum Safe Operating Area



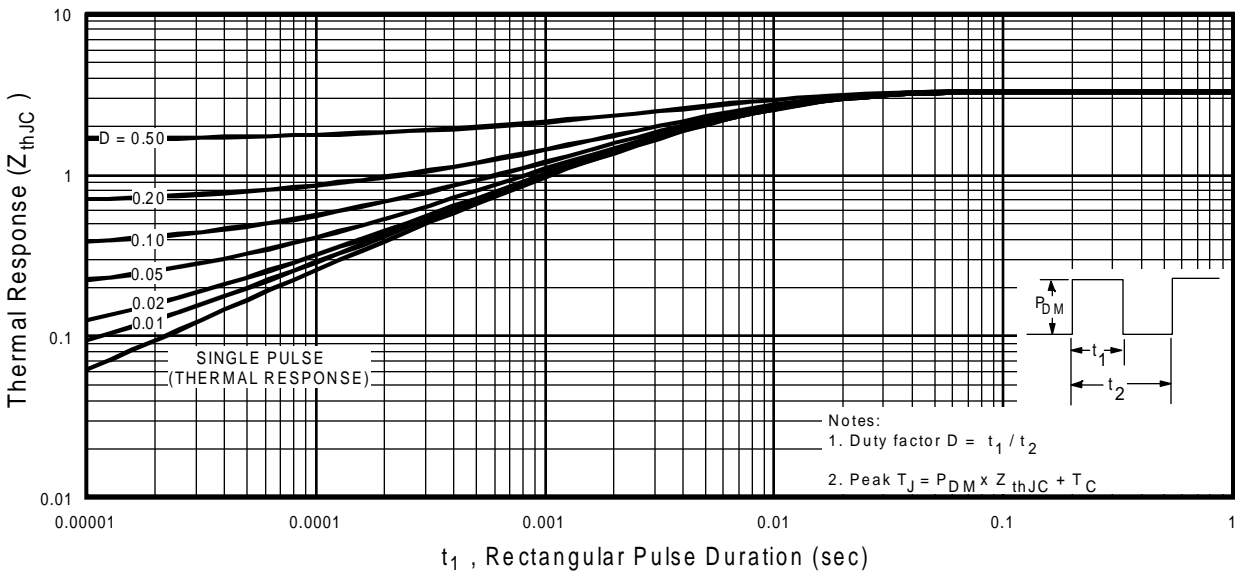
**Fig 9.** Maximum Drain Current Vs. Case Temperature



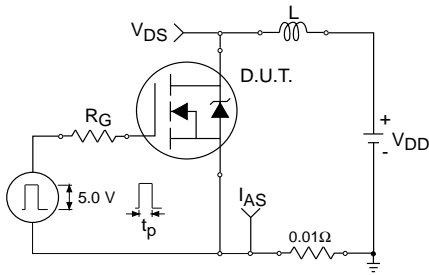
**Fig 10a.** Switching Time Test Circuit



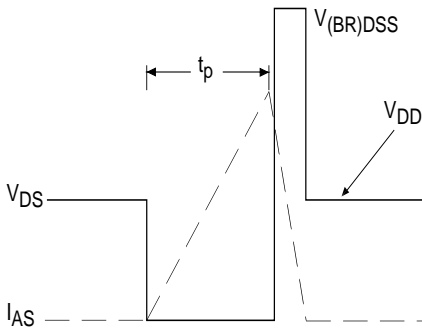
**Fig 10b.** Switching Time Waveforms



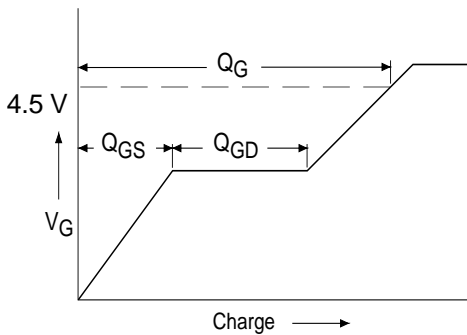
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



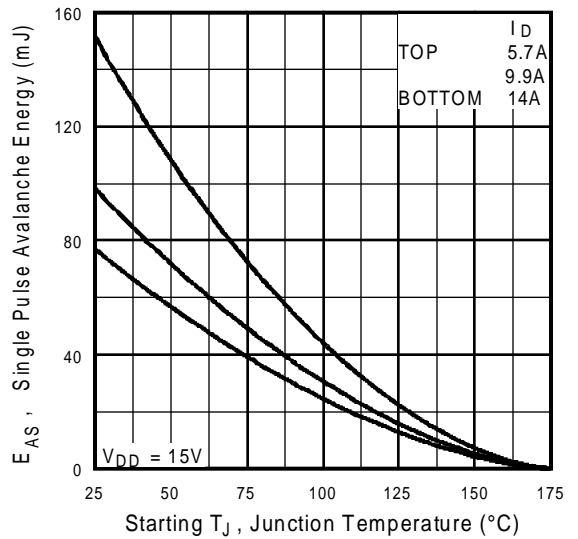
**Fig 12a.** Unclamped Inductive Test Circuit



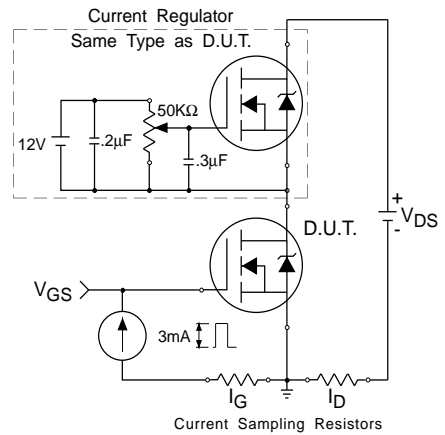
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

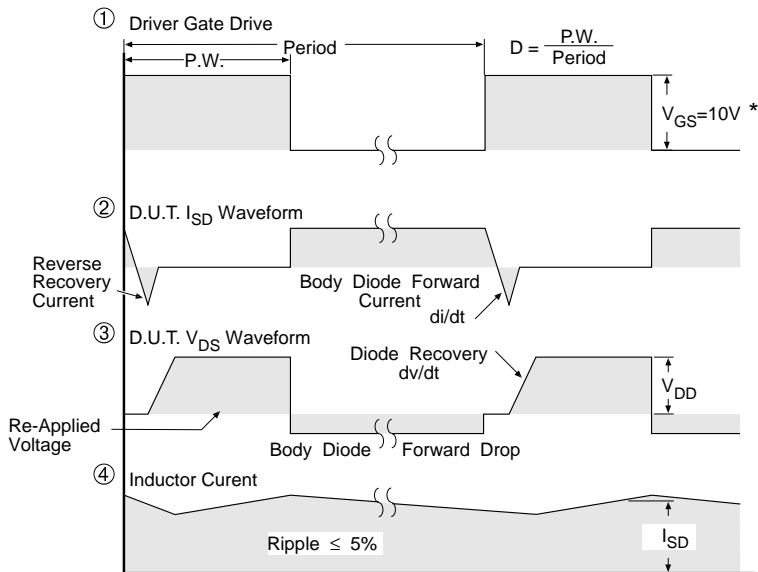


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

### Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

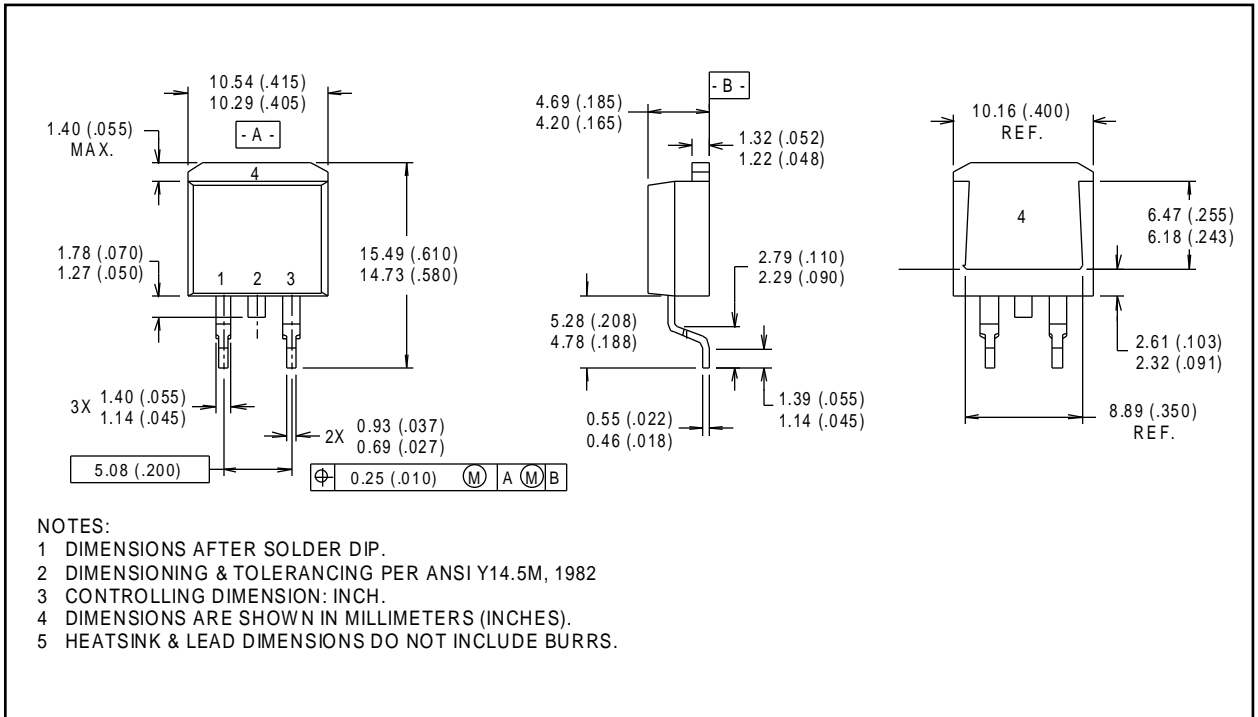
**Fig 14.** For N-Channel HEXFETS

# IRL2703S

## Package Outline

### D<sup>2</sup>Pak Outline

Dimensions are shown in millimeters (inches)



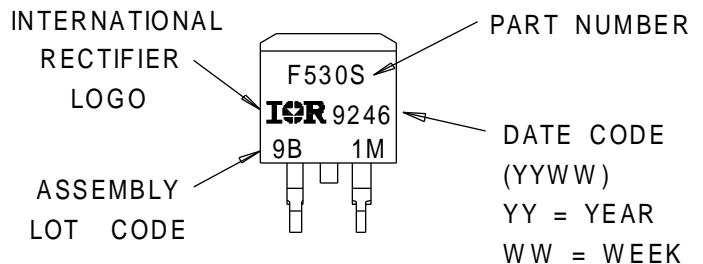
#### NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982
- 3 CONTROLLING DIMENSION: INCH.
- 4 DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- 5 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

## Part Marking Information

### D<sup>2</sup>Pak

EXAMPLE : THIS IS AN IRF530S  
WITH ASSEMBLY  
LOT CODE 9B1M





**Tape & Reel Information**

**D<sup>2</sup>Pak**

Dimensions are shown in millimeters (inches)

